

急出货

# High-Voltage Amplifier Transistor (150V, 50mA)

## 2SC5274

### ●Features

- 1) High breakdown voltage. ( $V_{CE0}=150V$ )
- 2) Low collector output capacitance, typically 2pF at  $V_{CB}=12V$ .

### ●Packaging specifications and hFE

Type	2SC5274
Package	EMT3
hFE	N
Marking	BV*
Code	TL
Basic ordering unit (pieces)	3000

\* Denotes hFE

### ●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	$BV_{CBO}$	150	—	—	V	$I_C=50\mu A$
Collector-emitter breakdown voltage	$BV_{CEO}$	150	—	—	V	$I_C=1mA$
Emitter-base breakdown voltage	$BV_{EBO}$	5	—	—	V	$I_E=50\mu A$
Collector cutoff current	$I_{CBO}$	—	—	0.5	$\mu A$	$V_{CB}=100V, I_E=0A$
Emitter cutoff current	$I_{EBO}$	—	—	0.5	$\mu A$	$V_{EB}=4V, I_C=0A$
Collector-emitter saturation voltage	$V_{CE(sat)}$	—	—	0.5	V	$I_C/I_E=10mA/1mA$
DC current transfer ratio	$h_{FE}$	56	—	120	—	$V_{CE}/I_C=10V/10mA$
Transition frequency	$f_T$	—	120	—	MHz	$V_{CE}=12V, I_E=-10mA, f=30MHz$
Output capacitance	$C_{ob}$	—	2	—	pF	$V_{CB}=12V, I_E=0A, f=1MHz$

### ●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-base voltage	$V_{CBO}$	150	V
Collector-emitter voltage	$V_{CEO}$	150	V
Emitter-base voltage	$V_{EBO}$	5	V
Collector current	$I_C$	50	mA (DC)
		0.2	A (Pulse) *
Collector power dissipation	$P_C$	0.15	W
Junction temperature	$T_J$	150	°C
Storage temperature	$T_{stg}$	-55~+150	°C

\* Single pulse Pw=100ms

(96-203-C329)

